

μ PA2806 MOS FIELD EFFECT TRANSISTOR

Description

The μ PA2806 is N-channel MOSFET designed for DC/DC converter and power management applications.

Features

- Low on-state resistance
 - R_{DS(on)1} = 57 m Ω MAX. (V_{GS} = 10 V, I_D = 10 A)
 - --- $R_{DS(on)2} = 70 \text{ m}\Omega \text{ MAX}$. ($V_{GS} = 8 \text{ V}$, $I_D = 10 \text{ A}$)
- Low C_{iss} : $C_{iss} = 780 \text{ pF TYP}$. ($V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, f = 1 MHz)
- Built-in gate protection diode
- Thin type surface mount package with heat spreader (8-pin HVSON)
- RoHS Compliant

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2806T1L-E1-AY ^{*1}	Pure Sn (Tin)	Tape 3000 p/reel	8-pin HVSON (3333)
μ PA2806T1L-E2-AY ^{*1}			typ. 0.028 g

Note: *1. Pb-free (This product does not contain Pb in external electrode.)

Absolute Maximum Ratings (T_A = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	100	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC) ($T_c = 25^{\circ}C$)	I _{D(DC)}	±21	A
Drain Current (pulse) *1	I _{D(pulse)}	±31	A
Total Power Dissipation *2	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	3.8	W
Total Power Dissipation $(T_c = 25^{\circ}C)^{*2}$	P _{T3}	52	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	–55 to +150	°C
Single Avalanche Current *3	I _{AS}	14.3	A
Single Avalanche Energy *3	E _{AS}	20.4	mJ

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

^{*}2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

*3. Starting T_{ch} = 25°C, V_{DD} = 50 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

Thermal Resistance

Channel to Ambient Thermal Resistance *1	Rth(ch-A)	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	R _{th(ch-C)}	2.4	°C/W

Note: *1. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

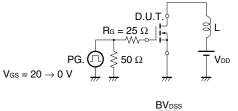


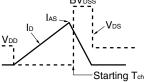
Electrical Characteristics (T_A = 25°C)

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			10	μA	V _{DS} = 100 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	V _{GS(off)}	2.0		4.0	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance *1	y _{fs}	5			S	V _{DS} = 10 V, I _D = 10 A
Drain to Source On-state	R _{DS(on)1}		47	57	mΩ	V_{GS} = 10 V, I_{D} = 10 A
Resistance *1	R _{DS(on)2}		49	70	mΩ	V_{GS} = 8 V, I_{D} = 10 A
Input Capacitance	C _{iss}		780		pF	V _{DS} = 10 V,
Output Capacitance	C _{oss}		150		pF	V _{GS} = 0 V,
Reverse Transfer Capacitance	C _{rss}		51		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		20		ns	V _{DD} = 50 V, I _D = 10 A,
Rise Time	t _r		10		ns	V _{GS} = 10 V,
Turn-off Delay Time	t _{d(off)}		46		ns	R _G = 10 Ω
Fall Time	t _f		7		ns	
Total Gate Charge	Q _G		18		nC	V _{DD} = 50 V,
Gate to Source Charge	Q _{GS}		5		nC	V _{GS} = 10 V,
Gate to Drain Charge	Q _{GD}		6		nC	I _D = 21 A
Body Diode Forward Voltage *1	V _{F(S-D)}		0.88		V	I _F = 21 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		50		ns	I _F = 21 A, V _{GS} = 0 V,
Reverse Recovery Charge	Q _{rr}		110		nC	di/dt = 100 A/ <i>µ</i> s
Gate Resistance	R _G		2.2		Ω	f = 1 MHz

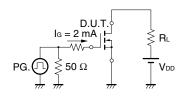
Note: *1. Pulsed

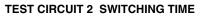
TEST CIRCUIT 1 AVALANCHE CAPABILITY



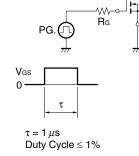


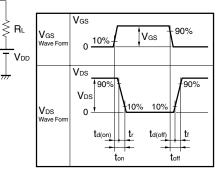
TEST CIRCUIT 3 GATE CHARGE





D.U.T.



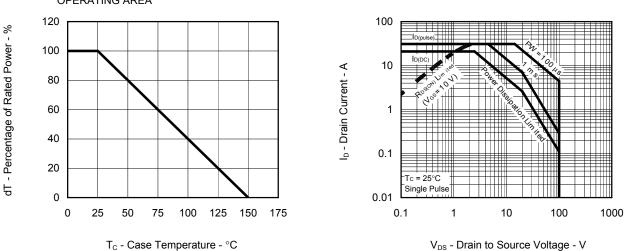




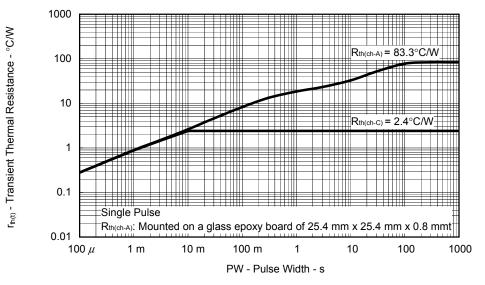
Typical Characteristics (T_A = 25°C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

FORWARD BIAS SAFE OPERATING AREA

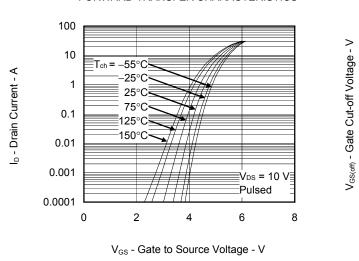


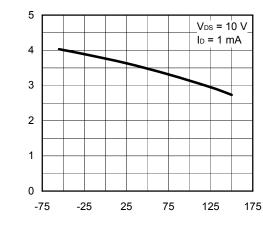




FORWARD TRANSFER CHARACTERISTICS

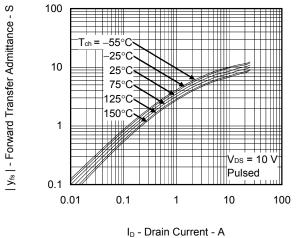
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE





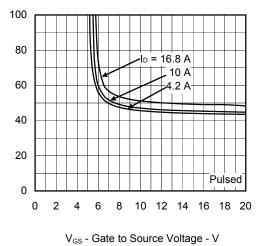
T_{ch} - Channel Temperature - °C

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

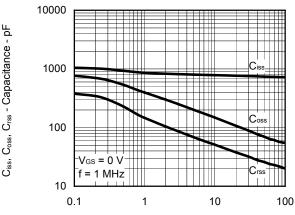




DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

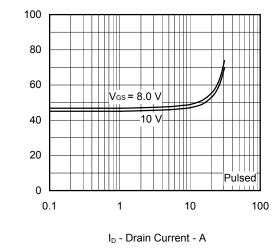


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



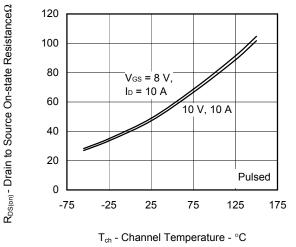
V_{DS} - Drain to Source Voltage - V

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

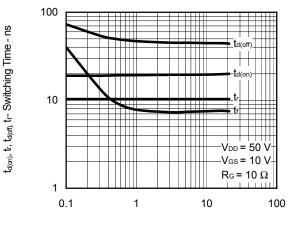


 $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



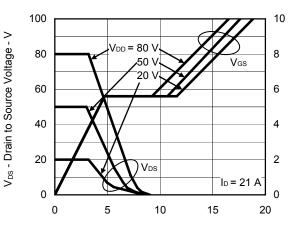
SWITCHING CHARACTERISTICS



I_D - Drain Current - A

Ciss, Coss, Crss - Capacitance - pF



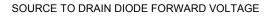


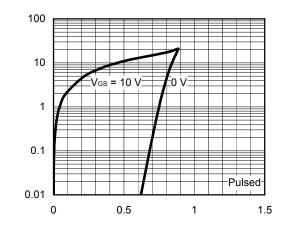
 $V_{\rm GS}$ - Gate to Source Voltage - V

I_F - Diode Forward Current - A

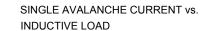
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

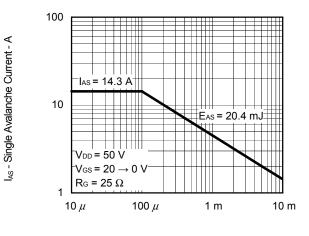
Q_G - Gate Charge - nC



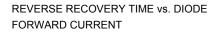


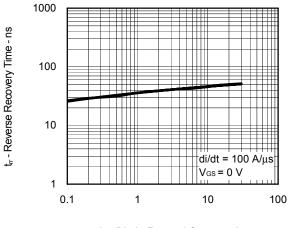
 $V_{\text{F(S-D)}}$ - Source to Drain Voltage - V





L - Inductive Load - H



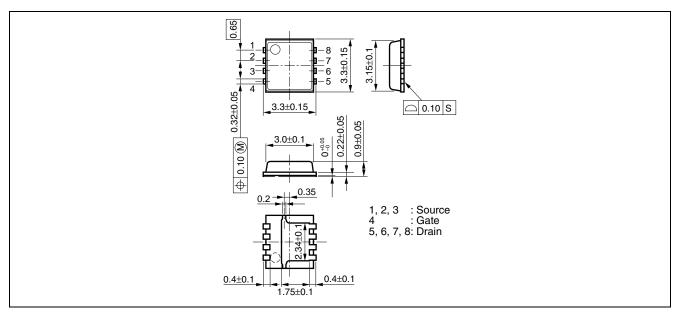


I_F - Diode Forward Current - A

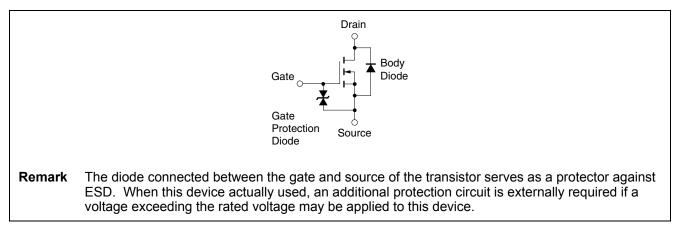


Package Drawings (Unit: mm)

8-pin HVSON (3333)



Equivalent Circuit





Revision History	μ ΡΑ2806

		Description			
Rev.	Date	Page	Summary		
1.00	June 01, 2010	-	First Eddition Issued		

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